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Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Active
Core Processor	ARM1136JF-S
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	532MHz
Co-Processors/DSP	Multimedia; GPU, IPU, MPEG-4, VFP
RAM Controllers	DDR
Graphics Acceleration	Yes
Display & Interface Controllers	Keyboard, Keypad, LCD
Ethernet	-
SATA	-
USB	USB 2.0 (3)
Voltage - I/O	1.8V, 2.0V, 2.5V, 2.7V, 3.0V
Operating Temperature	-20°C ~ 70°C (TA)
Security Features	Random Number Generator, RTIC, Secure Fusebox, Secure JTAG, Secure Memory
Package / Case	457-LFBGA
Supplier Device Package	457-MAPBGA (14x14)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcimx31ldvkn5d

Table 11. Fusebox Supply Current Parameters

Ref. Num	Description	Symbol	Minimum	Typical	Maximum	Units
1	eFuse Program Current. ¹ Current to program one eFuse bit: efuse_pgm = 3.0 V	I _{program}	—	35	60	mA
2	eFuse Read Current ² Current to read an 8-bit eFuse word vdd_fusebox = 1.875 V	I _{read}	—	5	8	mA

¹ The current I_{program} is during program time (t_{program}).

² The current I_{read} is present for approximately 50 ns of the read access to the 8-bit word, and only applies to Silicon Rev. 1.2 and previous.

4.1.1 Supply Current Specifications

Table 12 shows the core current consumption for -40°C to 85°C for Silicon Revision 2.0.1 for the MCIMX31.

Table 12. Current Consumption for -40°C to 85°C ^{1, 2} for Silicon Revision 2.0.1

Mode	Conditions	QVCC (Peripheral)		QVCC1 (ARM)		QVCC4 (L2)		FVCC + MVCC + SVCC + UVCC (PLL)		Unit
		Typ	Max	Typ	Max	Typ	Max	Typ	Max	
Deep Sleep	<ul style="list-style-type: none"> • QVCC = 0.95 V • ARM and L2 caches are power gated (QVCC1 = QVCC4 = 0 V) • All PLLs are off, VCC = 1.4 V • ARM is in well bias • FPM is off • 32 kHz input is on • CKIH input is off • CAMP is off • TCK input is off • All modules are off • No external resistive loads • RNGA oscillator is off 	0.16	5.50	—	—	—	—	0.02	0.10	mA
State Retention	<ul style="list-style-type: none"> • QVCC and QVCC1 = 0.95 V • L2 caches are power gated (QVCC4 = 0 V) • All PLLs are off, VCC = 1.4 V • ARM is in well bias • FPM is off • 32 kHz input is on • CKIH input is off • CAMP is off • TCK input is off • All modules are off • No external resistive loads • RNGA oscillator is off 	0.16	5.50	0.07	2.20	—	—	0.02	0.10	mA
Wait	<ul style="list-style-type: none"> • QVCC, QVCC1, and QVCC4 = 1.22 V • ARM is in wait for interrupt mode • MAX is active • L2 cache is stopped but powered • MCU PLL is on (532 MHz), VCC = 1.4 V • USB PLL and SPLL are off, VCC = 1.4 V • FPM is on • CKIH input is on • CAMP is on • 32 kHz input is on • All clocks are gated off • All modules are off (by programming CGR[2:0] registers) • RNGA oscillator is off • No external resistive loads 	6.00	15.00	2.20	25.00	0.03	0.29	3.60	4.40	mA

¹ Typical column: TA = 25°C

² Maximum column: TA = 85°C

Table 17. AC Electrical Characteristics of Fast¹ General I/O²

ID	Parameter	Symbol	Test Condition	Min	Typ	Max	Units
PA1	Output Transition Times (Max Drive)	tpr	25 pF 50 pF	0.68 1.34	1.33 2.6	2.07 4.06	ns
	Output Transition Times (High Drive)	tpr	25 pF 50 pF	.91 1.79	1.77 3.47	2.74 5.41	ns
	Output Transition Times (Std Drive)	tpr	25 pF 50 pF	1.36 2.68	2.64 5.19	4.12 8.11	ns

¹ Fast/slow characteristic is selected per GPIO (where available) by “slew rate” control. See reference manual.

² Use of GPIO in fast mode with the associated NVCC > 1.95 V can result in excessive overshoot and ringing.

Table 18. AC Electrical Characteristics of DDR I/O

ID	Parameter	Symbol	Test Condition	Min	Typ	Max	Units
PA1	Output Transition Times (DDR Drive) ¹	tpr	25 pF 50 pF	0.51 0.97	0.82 1.58	1.28 2.46	ns
	Output Transition Times (Max Drive)	tpr	25 pF 50 pF	0.67 1.29	1.08 2.1	1.69 3.27	ns
	Output Transition Times (High Drive)	tpr	25 pF 50 pF	.99 1.93	1.61 3.13	2.51 4.89	ns
	Output Transition Times (Std Drive)	tpr	25 pF 50 pF	1.96 3.82	3.19 6.24	4.99 9.73	ns

¹ Use of DDR Drive can result in excessive overshoot and ringing.

4.3.3 Clock Amplifier Module (CAMP) Electrical Characteristics

This section outlines the Clock Amplifier Module (CAMP) specific electrical characteristics. [Table 19](#) shows clock amplifier electrical characteristics.

Table 19. Clock Amplifier Electrical Characteristics for CKIH Input

Parameter	Min	Typ	Max	Units
Input Frequency	15	—	75	MHz
VIL (for square wave input)	0	—	0.3	V
VIH (for square wave input)	(VDD ¹ – 0.25)	—	3	V
Sinusoidal Input Amplitude	0.4 ²	—	VDD	Vp-p
Duty Cycle	45	50	55	%

¹ VDD is the supply voltage of CAMP. See reference manual.

² This value of the sinusoidal input will be measured through characterization.

4.3.4 1-Wire Electrical Specifications

Figure 6 depicts the RPP timing, and Table 20 lists the RPP timing parameters.

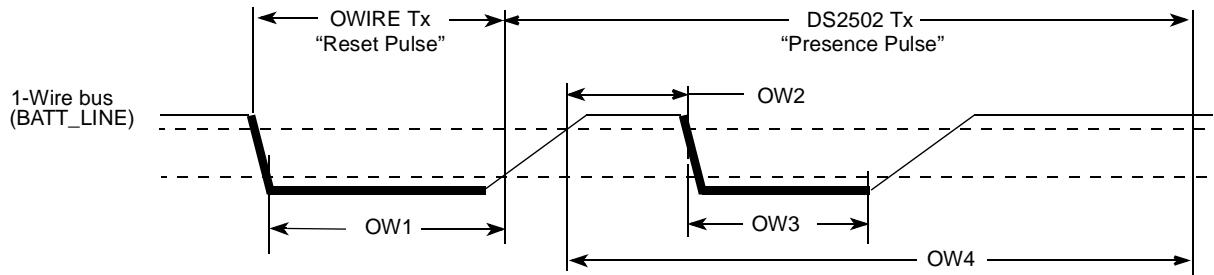


Figure 6. Reset and Presence Pulses (RPP) Timing Diagram

Table 20. RPP Sequence Delay Comparisons Timing Parameters

ID	Parameters	Symbol	Min	Typ	Max	Units
OW1	Reset Time Low	t_{RSTL}	480	511	—	μs
OW2	Presence Detect High	t_{PDH}	15	—	60	μs
OW3	Presence Detect Low	t_{PDL}	60	—	240	μs
OW4	Reset Time High	t_{RSTH}	480	512	—	μs

Figure 7 depicts Write 0 Sequence timing, and Table 21 lists the timing parameters.

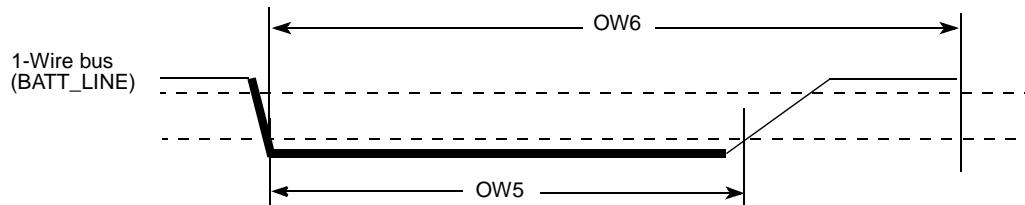


Figure 7. Write 0 Sequence Timing Diagram

Table 21. WR0 Sequence Timing Parameters

ID	Parameter	Symbol	Min	Typ	Max	Units
OW5	Write 0 Low Time	t_{WR0_low}	60	100	120	μs
OW6	Transmission Time Slot	t_{SLOT}	OW5	117	120	μs

Figure 8 depicts Write 1 Sequence timing, Figure 9 depicts the Read Sequence timing, and Table 22 lists the timing parameters.

4.3.5.2 PIO Mode Timing

Figure 10 shows timing for PIO read, and Table 24 lists the timing parameters for PIO read.

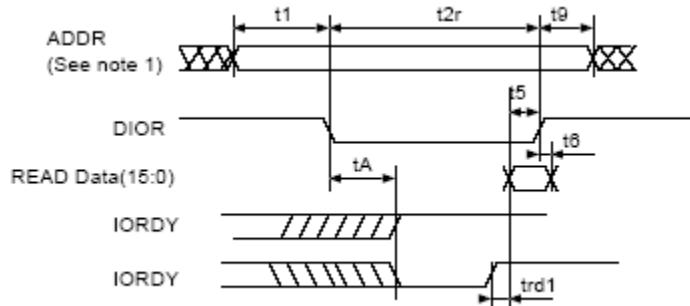


Figure 10. PIO Read Timing Diagram

Table 24. PIO Read Timing Parameters

ATA Parameter	Parameter from Figure 10	Value	Controlling Variable
t1	t1	$t1 \text{ (min)} = \text{time_1} * T - (\text{tskew1} + \text{tskew2} + \text{tskew5})$	time_1
t2	t2r	$t2 \text{ min} = \text{time_2r} * T - (\text{tskew1} + \text{tskew2} + \text{tskew5})$	time_2r
t9	t9	$t9 \text{ (min)} = \text{time_9} * T - (\text{tskew1} + \text{tskew2} + \text{tskew6})$	time_3
t5	t5	$t5 \text{ (min)} = \text{tco} + \text{tsu} + \text{tbuf} + \text{tbuf} + \text{tcable1} + \text{tcable2}$ If not met, increase time_2	—
t6	t6	0	—
tA	tA	$tA \text{ (min)} = (1.5 + \text{time_ax}) * T - (\text{tco} + \text{tsui} + \text{tcable2} + \text{tcable2} + 2 * \text{tbuf})$	time_ax
trd	trd1	$\text{trd1 (max)} = (-\text{trd}) + (\text{tskew3} + \text{tskew4})$ $\text{trd1 (min)} = (\text{time_pio_rdx} - 0.5) * T - (\text{tsu} + \text{thi})$ $(\text{time_pio_rdx} - 0.5) * T > \text{tsu} + \text{thi} + \text{tskew3} + \text{tskew4}$	time_pio_rdx
t0	—	$t0 \text{ (min)} = (\text{time_1} + \text{time_2} + \text{time_9}) * T$	time_1, time_2r, time_9

Figure 11 shows timing for PIO write, and Table 25 lists the timing parameters for PIO write.

Electrical Characteristics

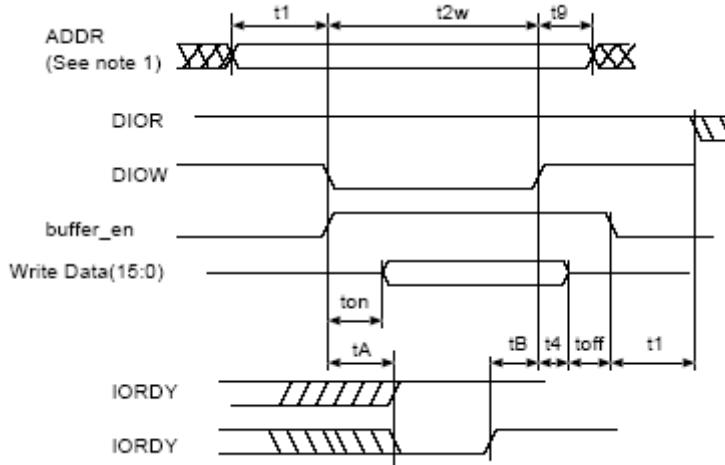


Figure 11. Multiword DMA (MDMA) Timing

Table 25. PIO Write Timing Parameters

ATA Parameter	Parameter from Figure 11	Value	Controlling Variable
t1	t1	$t1 \text{ (min)} = \text{time_1} * T - (\text{tskew1} + \text{tskew2} + \text{tskew5})$	time_1
t2	t2w	$t2 \text{ (min)} = \text{time_2w} * T - (\text{tskew1} + \text{tskew2} + \text{tskew5})$	time_2w
t9	t9	$t9 \text{ (min)} = \text{time_9} * T - (\text{tskew1} + \text{tskew2} + \text{tskew6})$	time_9
t3	—	$t3 \text{ (min)} = (\text{time_2w} - \text{time_on}) * T - (\text{tskew1} + \text{tskew2} + \text{tskew5})$	If not met, increase time_2w
t4	t4	$t4 \text{ (min)} = \text{time_4} * T - \text{tskew1}$	time_4
tA	tA	$tA = (1.5 + \text{time_ax}) * T - (\text{tco} + \text{tsui} + \text{tcable2} + \text{tcable2} + 2 * \text{tbuf})$	time_ax
t0	—	$t0(\text{min}) = (\text{time_1} + \text{time_2} + \text{time_9}) * T$	time_1, time_2r, time_9
—	—	Avoid bus contention when switching buffer on by making ton long enough.	—
—	—	Avoid bus contention when switching buffer off by making toff long enough.	—

Figure 12 shows timing for MDMA read, Figure 13 shows timing for MDMA write, and Table 26 lists the timing parameters for MDMA read and write.

Electrical Characteristics

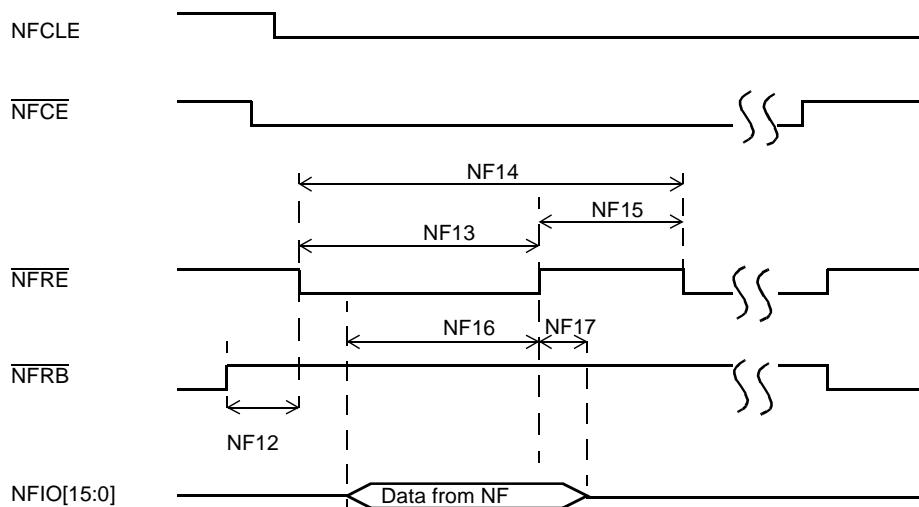


Figure 25. Read Data Latch Cycle Timing Diagram

Table 31. NFC Timing Parameters¹

ID	Parameter	Symbol	Timing $T = \text{NFC Clock Cycle}^2$		Example Timing for NFC Clock $\approx 33 \text{ MHz}$ $T = 30 \text{ ns}$		Unit
			Min	Max	Min	Max	
NF1	NFCLE Setup Time	tCLS	T-1.0 ns	—	29	—	ns
NF2	NFCLE Hold Time	tCLH	T-2.0 ns	—	28	—	ns
NF3	NFCE Setup Time	tCS	T-1.0 ns	—	29	—	ns
NF4	NFCE Hold Time	tCH	T-2.0 ns	—	28	—	ns
NF5	NF_WP Pulse Width	tWP	T-1.5 ns		28.5		ns
NF6	NFALE Setup Time	tALS	T	—	30	—	ns
NF7	NFALE Hold Time	tALH	T-3.0 ns	—	27	—	ns
NF8	Data Setup Time	tDS	T	—	30	—	ns
NF9	Data Hold Time	tDH	T-5.0 ns	—	25	—	ns
NF10	Write Cycle Time	tWC	2T		60		ns
NF11	NFWE Hold Time	tWH	T-2.5 ns		27.5		ns
NF12	Ready to NFRE Low	tRR	6T	—	180	—	ns
NF13	NFRE Pulse Width	tRP	1.5T	—	45	—	ns
NF14	READ Cycle Time	tRC	2T	—	60	—	ns
NF15	NFRE High Hold Time	tREH	0.5T-2.5 ns		12.5	—	ns
NF16	Data Setup on READ	tDSR	N/A		10	—	ns
NF17	Data Hold on READ	tDHR	N/A		0	—	ns

¹ The flash clock maximum frequency is 50 MHz.

² Subject to DPLL jitter specification on [Table 30, "DPLL Specifications," on page 35](#).

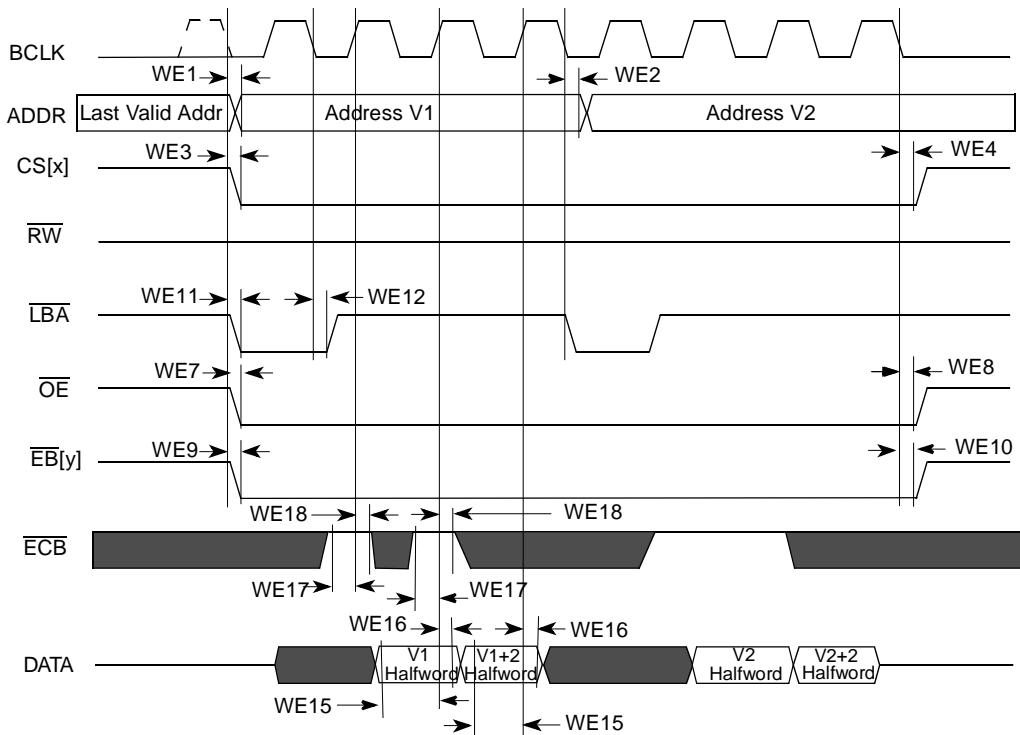


Figure 29. Synchronous Memory Timing Diagram for Two Non-Sequential Read Accesses—
WSC=2, SYNC=1, DOL=0

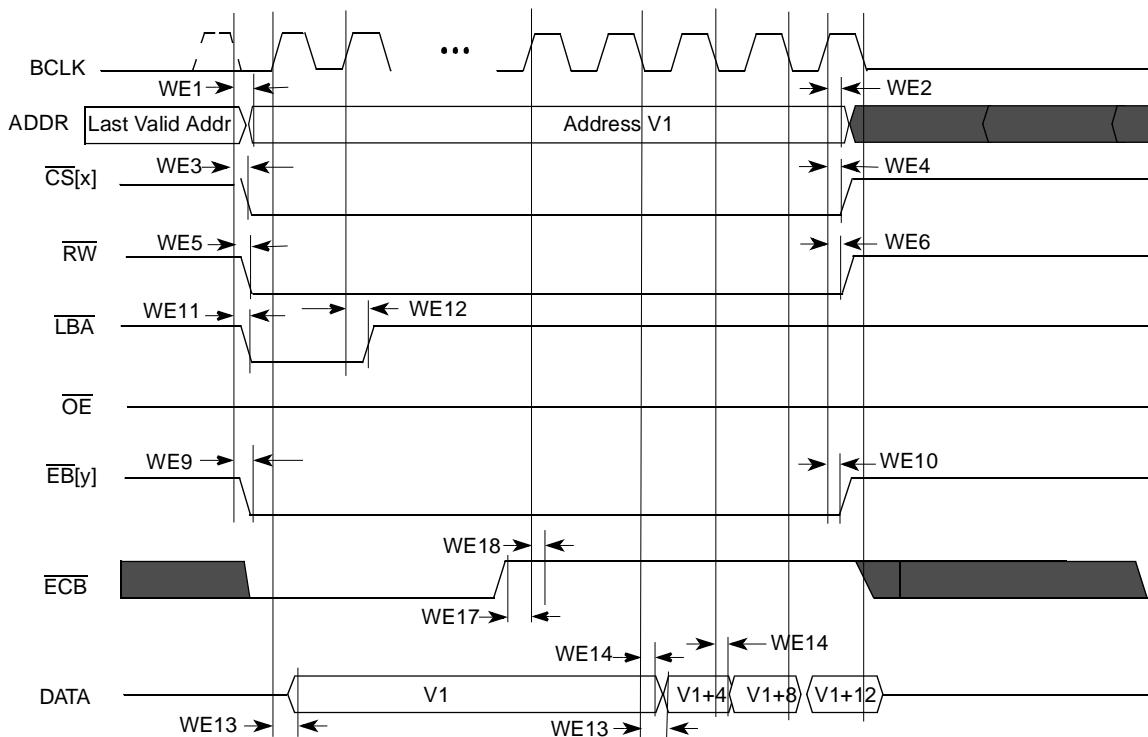
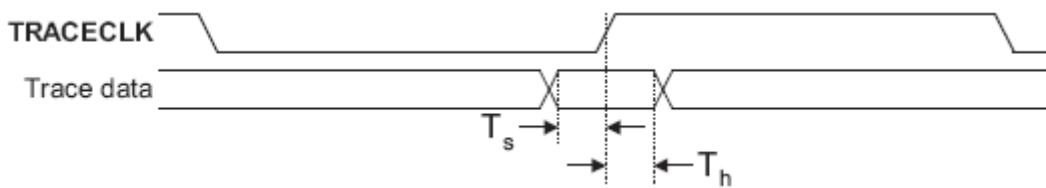


Figure 30. Synchronous Memory Timing Diagram for Burst Write Access—
BCS=1, WSC=4, SYNC=1, DOL=0, PSR=1

Table 39. ETM TRACECLK Timing Parameters

ID	Parameter	Min	Max	Unit
T _{cyc}	Clock period	Frequency dependent	—	ns
T _{wl}	Low pulse width	2	—	ns
T _{wh}	High pulse width	2	—	ns
T _r	Clock and data rise time	—	3	ns
T _f	Clock and data fall time	—	3	ns

Figure 40 depicts the setup and hold requirements of the trace data pins with respect to TRACECLK, and Table 40 lists the timing parameters.

**Figure 40. Trace Data Timing Diagram****Table 40. ETM Trace Data Timing Parameters**

ID	Parameter	Min	Max	Unit
T _s	Data setup	2	—	ns
T _h	Data hold	1	—	ns

4.3.10.1 Half-Rate Clocking Mode

When half-rate clocking is used, the trace data signals are sampled by the TPA on both the rising and falling edges of TRACECLK, where TRACECLK is half the frequency of the clock shown in Figure 40.

4.3.11 FIR Electrical Specifications

FIR implements asynchronous infrared protocols (FIR, MIR) that are defined by IrDA® (Infrared Data Association). Refer to <http://www.IrDA.org> for details on FIR and MIR protocols.

4.3.12 Fusebox Electrical Specifications

Table 41. Fusebox Timing Characteristics

Ref. Num	Description	Symbol	Minimum	Typical	Maximum	Units
1	Program time for eFuse ¹	t _{program}	125	—	—	μs

¹ The program length is defined by the value defined in the epm_pgm_length[2:0] bits of the IIM module. The value to program is based on a 32 kHz clock source ($4 * 1/32 \text{ kHz} = 125 \mu\text{s}$).

Electrical Characteristics

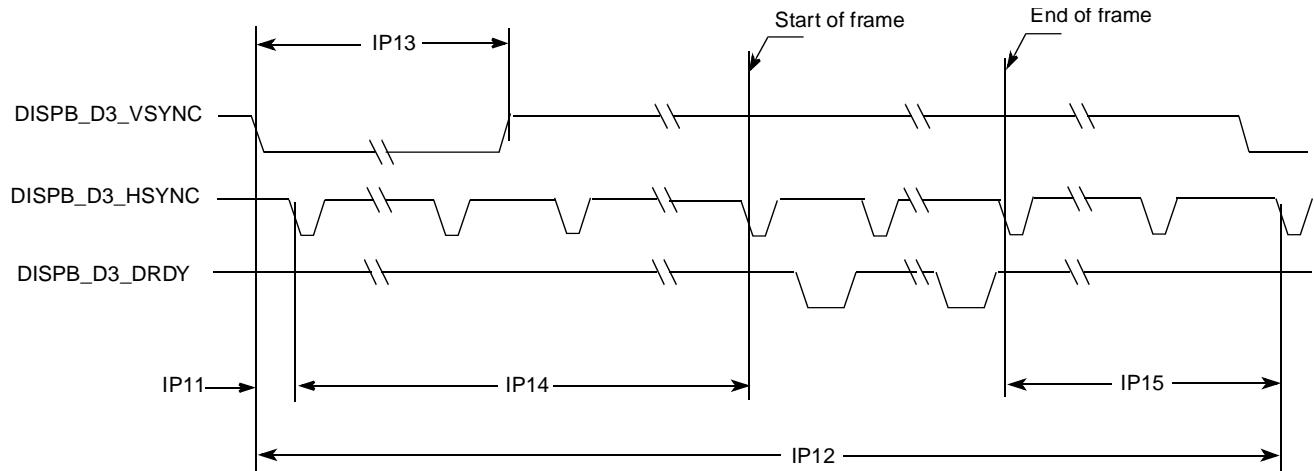


Figure 47. TFT Panels Timing Diagram—Vertical Sync Pulse

Table 46 shows timing parameters of signals presented in Figure 46 and Figure 47.

Table 46. Synchronous Display Interface Timing Parameters—Pixel Level

ID	Parameter	Symbol	Value	Units
IP5	Display interface clock period	Tdicp	Tdicp ¹	ns
IP6	Display pixel clock period	Tdpccp	(DISP3_IF_CLK_CNT_D+1) * Tdicp	ns
IP7	Screen width	Tsw	(SCREEN_WIDTH+1) * Tdpccp	ns
IP8	Hsync width	Thsw	(H_SYNC_WIDTH+1) * Tdpccp	ns
IP9	Horizontal blank interval 1	Thbi1	BGXP * Tdpccp	ns
IP10	Horizontal blank interval 2	Thbi2	(SCREEN_WIDTH - BGXP - FW) * Tdpccp	ns
IP11	Hsync delay	Thsd	H_SYNC_DELAY * Tdpccp	ns
IP12	Screen height	Tsh	(SCREEN_HEIGHT+1) * Tsw	ns
IP13	Vsync width	Tvsw	if V_SYNC_WIDTH_L = 0 then (V_SYNC_WIDTH+1) * Tdpccp else (V_SYNC_WIDTH+1) * Tsw	ns
IP14	Vertical blank interval 1	Tvbi1	BGYP * Tsw	ns
IP15	Vertical blank interval 2	Tvbi2	(SCREEN_HEIGHT - BGYP - FH) * Tsw	ns

¹ Display interface clock period immediate value.

$$T_{dicp} = \begin{cases} T_{HSP_CLK} \cdot \frac{\text{DISP3_IF_CLK_PER_WR}}{\text{HSP_CLK_PERIOD}}, & \text{for integer } \frac{\text{DISP3_IF_CLK_PER_WR}}{\text{HSP_CLK_PERIOD}} \\ T_{HSP_CLK} \cdot \left(\text{floor} \left[\frac{\text{DISP3_IF_CLK_PER_WR}}{\text{HSP_CLK_PERIOD}} \right] + 0.5 \pm 0.5 \right), & \text{for fractional } \frac{\text{DISP3_IF_CLK_PER_WR}}{\text{HSP_CLK_PERIOD}} \end{cases}$$

Display interface clock period average value.

$$\bar{T}_{dicp} = T_{HSP_CLK} \cdot \frac{\text{DISP3_IF_CLK_PER_WR}}{\text{HSP_CLK_PERIOD}}$$

Electrical Characteristics

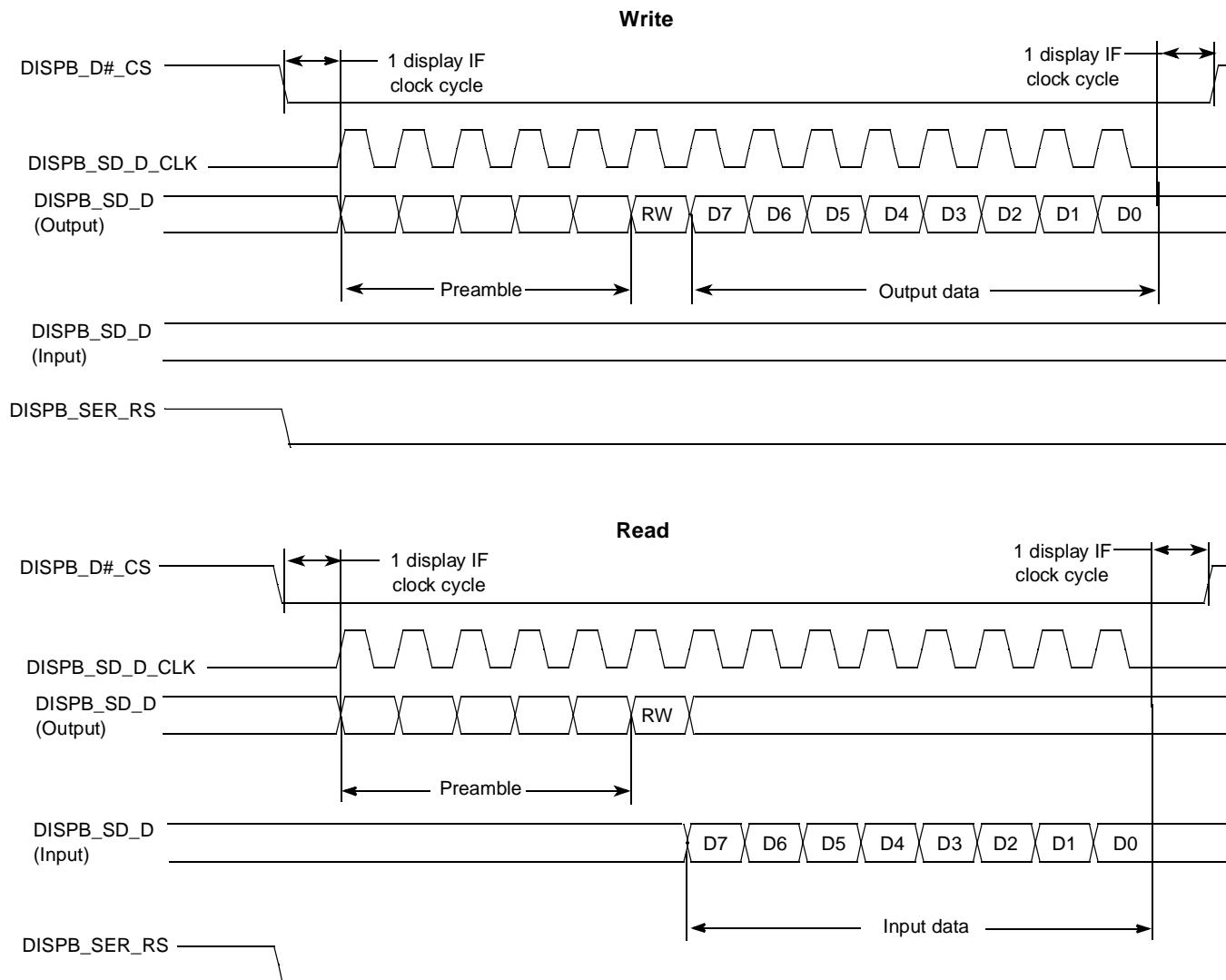


Figure 62. 5-Wire Serial Interface (Type 1) Timing Diagram

Electrical Characteristics

The DISP#_IF_CLK_PER_WR, DISP#_IF_CLK_PER_RD, HSP_CLK_PERIOD, DISP#_IF_CLK_DOWN_WR, DISP#_IF_CLK_UP_WR, DISP#_IF_CLK_DOWN_RD, DISP#_IF_CLK_UP_RD and DISP#_READ_EN parameters are programmed via the DI_DISP#_TIME_CONF_1, DI_DISP#_TIME_CONF_2 and DI_HSP_CLK_PER Registers.

4.3.16 Memory Stick Host Controller (MSHC)

Figure 65, Figure 66, and Figure 67 depict the MSHC timings, and Table 51 and Table 52 list the timing parameters.

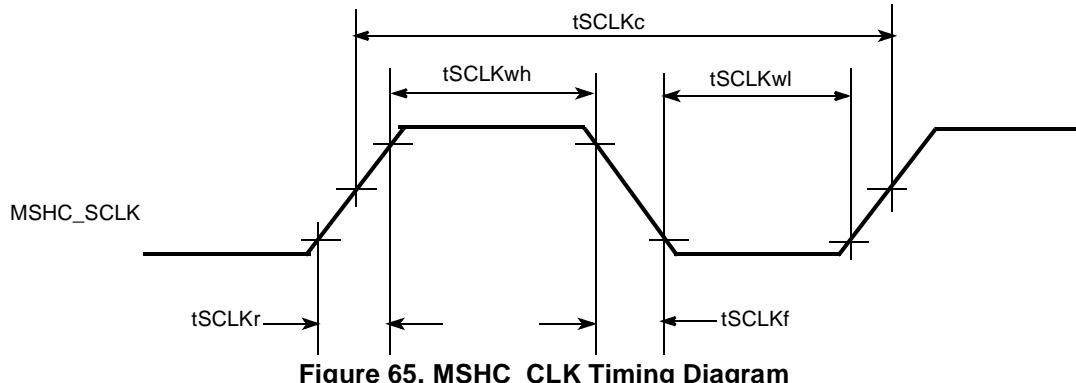


Figure 65. MSHC_CLK Timing Diagram

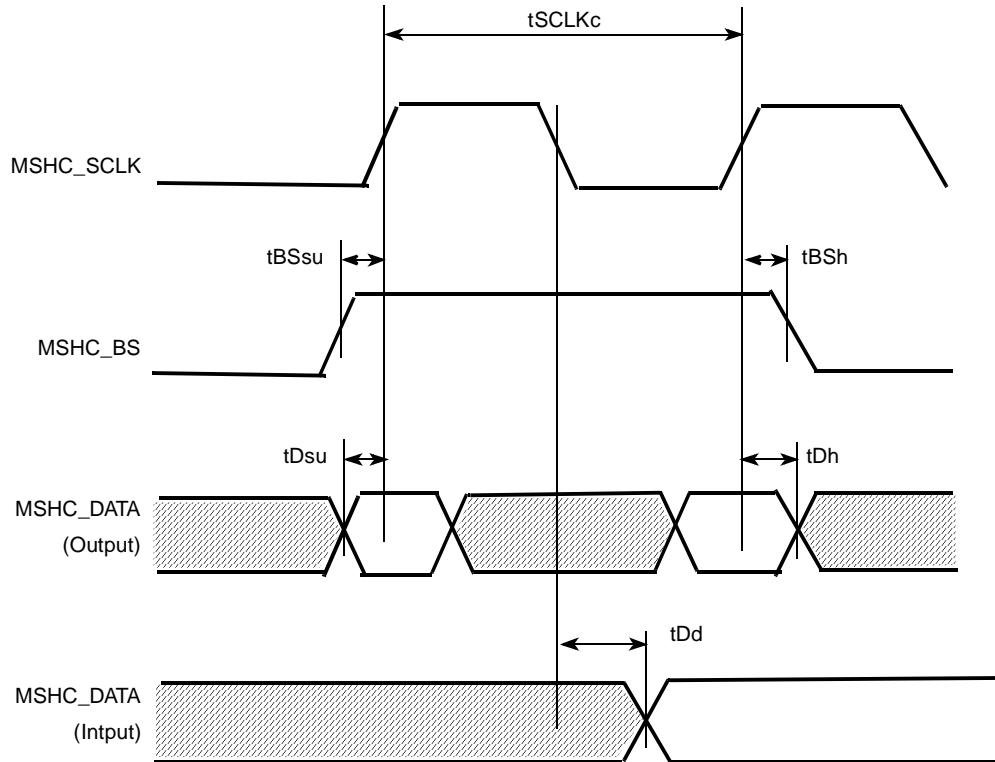


Figure 66. Transfer Operation Timing Diagram (Serial)

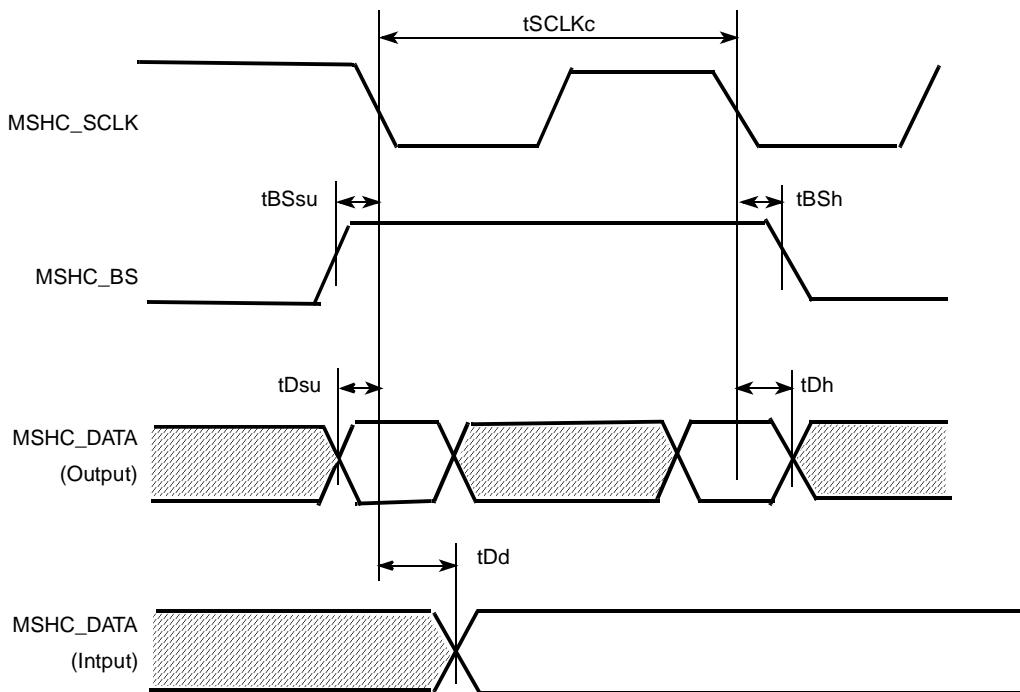


Figure 67. Transfer Operation Timing Diagram (Parallel)

NOTE

The Memory Stick Host Controller is designed to meet the timing requirements per Sony's *Memory Stick Pro Format Specifications* document. Tables in this section details the specifications requirements for parallel and serial modes, and not the MCIMX31 timing.

Table 51. Serial Interface Timing Parameters¹

Signal	Parameter	Symbol	Standards		Unit
			Min.	Max.	
MSHC_SCLK	Cycle	tSCLKc	50	—	ns
	H pulse length	tSCLKwh	15	—	ns
	L pulse length	tSCLKwl	15	—	ns
	Rise time	tSCLKr	—	10	ns
	Fall time	tSCLKf	—	10	ns
MSHC_BS	Setup time	tBSSu	5	—	ns
	Hold time	tBSh	5	—	ns
MSHC_DATA	Setup time	tDsu	5	—	ns
	Hold time	tDh	5	—	ns
	Output delay time	tDd	—	15	ns

¹ Timing is guaranteed for NVCC from 2.7 through 3.1 V and up to a maximum overdrive NVCC of 3.3 V. See NVCC restrictions described in Table 8, "Operating Ranges," on page 13.

Electrical Characteristics

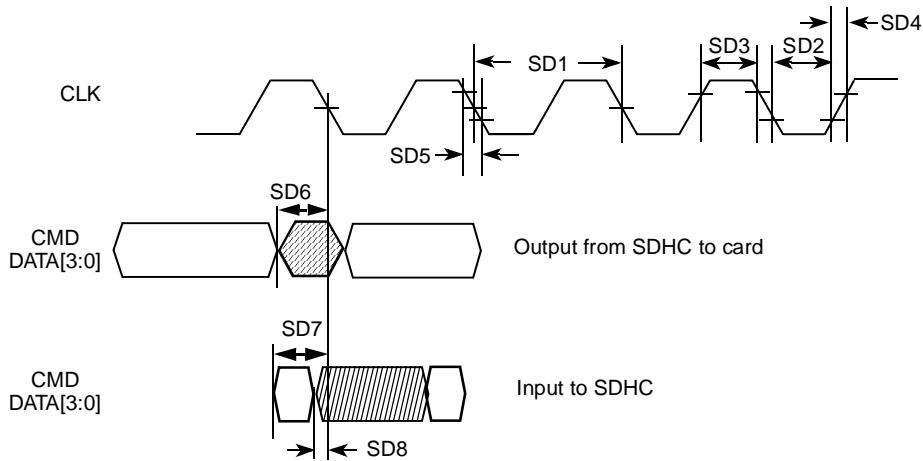


Figure 71. SDHC Timing Diagram

Table 55. SDHC Interface Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
Card Input Clock					
SD1	Clock Frequency (Low Speed)	f_{PP}^1	0	400	kHz
	Clock Frequency (SD/SDIO Full Speed)	f_{PP}^2	0	25	MHz
	Clock Frequency (MMC Full Speed)	f_{PP}^3	0	20	MHz
	Clock Frequency (Identification Mode)	f_{OD}^4	100	400	kHz
SD2	Clock Low Time	t_{WL}	10	—	ns
SD3	Clock High Time	t_{WH}	10	—	ns
SD4	Clock Rise Time	t_{TLH}	—	10	ns
SD5	Clock Fall Time	t_{THL}	—	10	ns
SDHC Output/Card Inputs CMD, DAT (Reference to CLK)					
SD6	SDHC output delay	t_{ODL}	-6.5	3	ns
SDHC Input/Card Outputs CMD, DAT (Reference to CLK)					
SD7	SDHC input setup	t_{IS}	—	18.5	ns
SD8	SDHC input hold	t_{IH}	—	-11.5	ns

¹ In low speed mode, card clock must be lower than 400 kHz, voltage ranges from 2.7 V–3.3 V.

² In normal data transfer mode for SD/SDIO card, clock frequency can be any value between 0 MHz–25 MHz.

³ In normal data transfer mode for MMC card, clock frequency can be any value between 0 MHz–20 MHz.

⁴ In card identification mode, card clock must be 100 kHz–400 kHz, voltage ranges from 2.7 V–3.3 V.

4.3.20 SIM Electrical Specifications

Each SIM card interface consist of a total of 12 pins (for 2 separate ports of 6 pins each. Mostly one port with 5 pins is used).

4.3.20.3 Power Down Sequence

Power down sequence for SIM interface is as follows:

1. SIMPD port detects the removal of the SIM Card
2. RST goes Low
3. CLK goes Low
4. TX goes Low
5. VEN goes Low

Each of this steps is done in one CKIL period (usually 32 kHz). Power down can be started because of a SIM Card removal detection or launched by the processor. [Figure 75](#) and [Table 57](#) show the usual timing requirements for this sequence, with F_{CKIL} = CKIL frequency value.

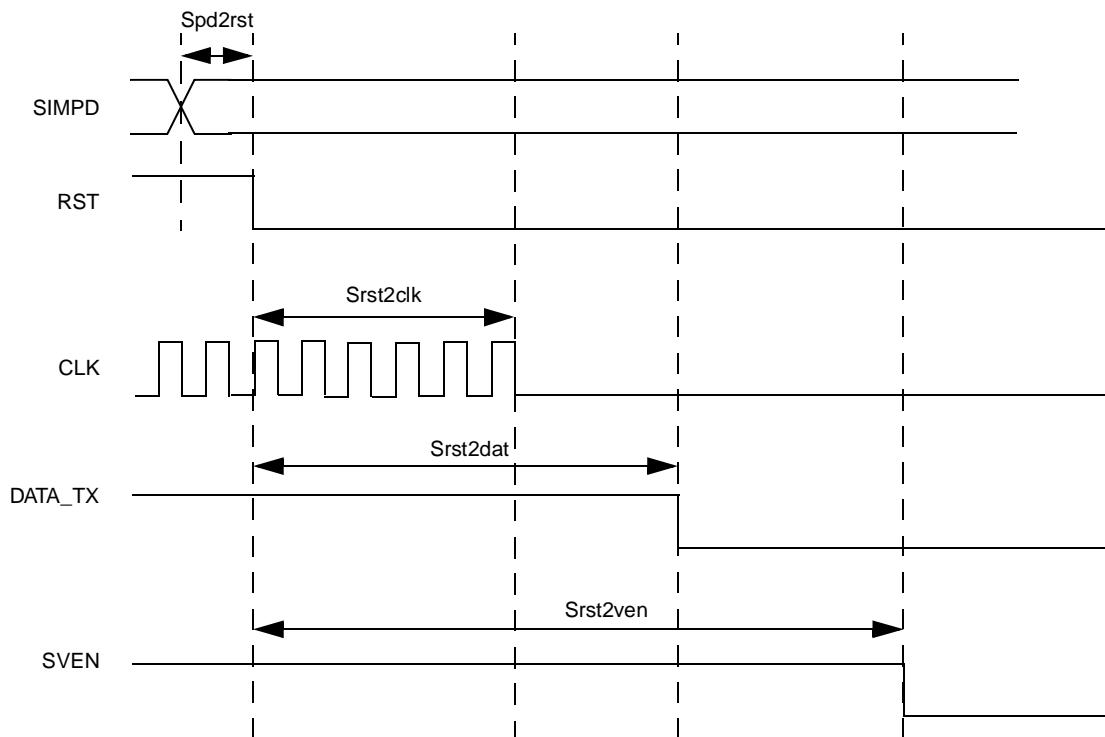


Figure 75. SmartCard Interface Power Down AC Timing

Table 57. Timing Requirements for Power Down Sequence

Num	Description	Symbol	Min	Max	Unit
1	SIM reset to SIM clock stop	$S_{rst2clk}$	$0.9*1/F_{CKIL}$	0.8	μs
2	SIM reset to SIM TX data low	$S_{rst2dat}$	$1.8*1/F_{CKIL}$	1.2	μs
3	SIM reset to SIM Voltage Enable Low	$S_{rst2ven}$	$2.7*1/F_{CKIL}$	1.8	μs
4	SIM Presence Detect to SIM reset Low	S_{pd2rst}	$0.9*1/F_{CKIL}$	25	ns

Package Information and Pinout

Table 65. 14 x 14 BGA Signal ID by Ball Grid Location (continued)

Signal ID	Ball Location	Signal ID	Ball Location
CSPI3_SCLK	E1	GPIO1_3	F25
CSPI3_SPI_RDY	G6	GPIO1_4	F19
CTS1	B11	GPIO1_5 (PWR RDY)	B24
CTS2	G13	GPIO1_6	A23
D0	AB2	GPIO3_0	K21
D1	Y3	GPIO3_1	H26
D10	Y1	HSYNC	N25
D11	U7	I2C_CLK	J24
D12	W2	I2C_DAT	H25
D13	V3	IOIS16	J3
D14	W1	KEY_COL0	C15
D15	U6	KEY_COL1	B17
D2	AB1	KEY_COL2	G15
D3	W6	KEY_COL3	A17
D3_CLS	R20	KEY_COL4	C16
D3_REV	T26	KEY_COL5	B18
D3_SPL	U25	KEY_COL6	F15
D4	AA2	KEY_COL7	A18
D5	V7	KEY_ROW0	F13
D6	AA1	KEY_ROW1	B15
D7	W3	KEY_ROW2	C14
D8	Y2	KEY_ROW3	A15
D9	V6	KEY_ROW4	G14
DCD_DCE1	B12	KEY_ROW5	B16
DCD_DTE1	B13	KEY_ROW6	F14
DE	C18	KEY_ROW7	A16
DQM0	AE19	L2PG	See VPG1
DQM1	AD19	LBA	AE22
DQM2	AA20	LCS0	P26
DQM3	AE18	LCS1	P21
DRDY0	N26	LD0	T24
DSR_DCE1	A11	LD1	U26
DSR_DTE1	A12	LD10	V24
DTR_DCE1	C11	LD11	Y25
DTR_DCE2	F12	LD12	Y26
DTR_DTE1	C12	LD13	V21
DVFS0	E25	LD14	AA25
DVFS1	G24	LD15	W24
EB0	W21	LD16	AA26
EB1	Y24	LD17	V20
ECB	AD23	LD2	T21
FPSHIFT	N21	LD3	V25
GPIO1_0	F18	LD4	T20
GPIO1_1	B23	LD5	V26
GPIO1_2	C20	LD6	U24
LD7	W25	SCK6	T2

5.2.2 MAPBGA Signal Assignment—19 × 19 mm 0.8 mm

See [Table 70](#) for the 19 × 19 mm, 0.8 mm pitch signal assignments/ball map.

5.2.3 Connection Tables—19 x 19 mm 0.8 mm

[Table 66](#) shows the device connection list for power and ground, alpha-sorted followed by [Table 67](#), which shows the no-connects. [Table 68](#) shows the device connection list for signals.

5.2.3.1 Ground and Power ID Locations—19 x 19 mm 0.8 mm

Table 66. 19 x 19 BGA Ground/Power ID by Ball Grid Location

GND/PWR ID	Ball Location
FGND	U16
FUSE_VDD	T15
FVCC	T16
GND	A1, A2, A3, A21, A22, A23, B1, B2, B22, B23, C1, C2, C22, C23, D22, D23, J12, J13, K10, K11, K12, K13, K14, L10, L11, L12, L13, L14, M9, M10, M11, M12, M13, M14, N10, N11, N12, N13, N14, P10, P11, P12, P13, P14, R12, Y1, Y23, AA1, AA2, AA22, AA23, AB1, AB2, AB21, AB22, AB23, AC1, AC2, AC21, AC22, AC23
IOQVDD	T8
MGND	U14
MVCC	U15
NVCC1	G15, G16, H16, J17
NVCC2	N16, P16, R15, R16, T14
NVCC3	K7, K8, L7, L8
NVCC4	H14, J15, K15
NVCC5	G9, G10, H8, H9
NVCC6	G11, G12, G13, H12
NVCC7	H15, J16, K16, L16, M16
NVCC8	H10, H11, J11
NVCC9	G14
NVCC10	P8, R7, R8, R9, T9
NVCC21	T11, T12, T13, U11
NVCC22	T10, U7, U8, U9, U10, V6, V7, V8, V9, V10
QVCC	H13, J14, L15, M15, N9, N15, P9, P15, R10, R11, R13, R14
QVCC1	J8, J9, J10, K9
QVCC4	L9, M7, M8, N8
SGND	U13
SVCC	U12
UVCC	P18
UGND	P17

Table 68. 19 x 19 BGA Signal ID by Ball Grid Location (continued)

Signal ID	Ball Location	Signal ID	Ball Location
DVFS1	E23	LD15	V21
EB0	W22	LD16	V20
EB1	W21	LD17	W23
ECB	Y21	LD2	R21
FPSHIFT	M23	LD3	R20
GPIO1_0	C19	LD4	T23
GPIO1_1	G17	LD5	T22
GPIO1_2	B20	LD6	T21
LD7	T20	SCK6	R2
LD8	R17	SCLK0	B19
LD9	U23	SD_D_CLK	M21
M_GRANT	U18	SD_D_I	M20
M_REQUEST	T17	SD_D_IO	M18
MA10	Y2	SD0	AC18
MCUPG	See VPG0	SD1	AA17
NFALE	T2	SD1_CLK	K2
NFCE	R4	SD1_CMD	K3
NFCLE	T1	SD1_DATA0	K4
NFRB	R3	SD1_DATA1	J1
NFRE	T4	SD1_DATA2	J2
NFWE	T3	SD1_DATA3	L6
NFWP	P6	SD10	AB14
OE	T18	SD11	AC14
PAR_RS	P22	SD12	AA13
PC_BVD1	G2	SD13	AB13
PC_BVD2	H4	SD14	AC13
PC_CD1	J3	SD15	AA12
PC_CD2	H1	SD16	AC12
PC_POE	J6	SD17	AA11
PC_PWRON	K6	SD18	AB11
PC_READY	H2	SD19	AC11
PC_RST	F1	SD2	AB17
PC_RW	G3	SD20	AA10
PC_VS1	H3	SD21	AB10
PC_VS2	G1	SD22	AC10
PC_WAIT	J4	SD23	AC9
POR	F21	SD24	AA9
POWER_FAIL	F20	SD25	AC8
PWMO	F2	SD26	AB8
RAS	AA19	SD27	AC7
READ	N18	SD28	AA8
RESET_IN	F22	SD29	AB7
RI_DCE1	D10	SD3	AC17
RI_DTE1	B11	SD30	AA7
RTCK	D15	SD31	AC6
RTS1	B9	SD4	AA16

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Table 68. 19 x 19 BGA Signal ID by Ball Grid Location (continued)

Signal ID	Ball Location	Signal ID	Ball Location
RTS2	B12	SD5	AC16
RW	V18	SD6	AA15
RXD1	C9	SD7	AB15
RXD2	A12	SD8	AC15
SCK3	P1	SD9	AA14
SCK4	G6	SDBA0	AA6
SCK5	D4	SDBA1	Y7
SDCKE0	Y17	TRSTB	F15
SDCKE1	V16	TXD1	D9
SDCLK	AC20	TXD2	F11
SDCLK	AC19	USB_BYP	C8
SDQS0	AB16	USB_OC	B8
SDQS1	AB12	USB_PWR	A8
SDQS2	AB9	USBH2_CLK	L1
SDQS3	AB6	USBH2_DATA0	M6
SDWE	AB20	USBH2_DATA1	K1
SER_RS	P23	USBH2_DIR	L2
SFS3	P2	USBH2_NXT	L4
SFS4	D3	USBH2_STP	L3
SFS5	G7	USBOTG_CLK	D8
SFS6	P4	USBOTG_DATA0	G8
SIMPDO	B18	USBOTG_DATA1	C7
SJC_MOD	C17	USBOTG_DATA2	A6
SRST0	C18	USBOTG_DATA3	F8
SRX0	A19	USBOTG_DATA4	D7
SRXD3	N3	USBOTG_DATA5	B6
SRXD4	C3	USBOTG_DATA6	A5
SRXD5	C4	USBOTG_DATA7	C6
SRXD6	R1	USBOTG_DIR	A7
STX0	F16	USBOTG_NXT	B7
STXD3	N4	USBOTG_STP	F9
STXD4	B3	VPG0	G21
STXD5	D1	VPG1	G22
STXD6	P3	VSTBY	H18
SVEN0	D17	VSYNC0	L22
TCK	F14	VSYNC3	N20
TDI	A18	WATCHDOG_RST	B21
TDO	B17	WRITE	N22
TMS	C16		

5.3 Ball Maps

Table 69. Ball Map—14 x 14 0.5 mm Pitch

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	
A	GND	GND	SFS5	CSP12_MISO	CSP12_SS2	USBOT_G_DAT_A7	USBOT_G_NXT_A3	USBOT_BYP	RXD1	DSR_D_CE1	DSR_D_TE1	RXD2	CE_CO_NTROL	KEY_R_OW3	KEY_R_OW7	KEY_C_OL3	KEY_C_OL7	TDO	SJC_MOD	SVEN0	CAPTURE	GPIO1_6	WATCHDOG_RST	GND	GND		
B	GND	GND	STXD4	SRXD5	CSP12_SS0	USBOT_G_DAT_A5	USBOT_G_DIR	USBOT_P_WB	CTS1	DCD_D_CE1	DCD_D_TE1	RTS2	KEY_R_OW1	KEY_R_OW5	KEY_C_OL1	KEY_C_OL5	TCK	TRSTB	SRX0	SCLK0	GPIO1_1	GPIO1_5	GND	GND			
C	GND	GND	SRXD4	SCK4	STXD5	CSP12_SS1	CSP12_SCLK	USBOT_G_DAT_A4	USBOT_G_STP	USBOT_O_C	DTR_D_CE1	DTR_D_TE1	TXD2	KEY_R_OW2	KEY_C_OL0	KEY_C_OL4	RTCK	DE	SRST0	GPIO1_2	BOOT_MODE1	BOOT_MODE3	CLK0	GND	GND	GND	
D	GND	CSP13_MOSI	SCK5																					BOOT_MODE2	GND	BOOT_MODE4	
E	CSP13_SCLK	ATA_DI_OR	CSP12_MOSI		NVCC5																			GND	DVFS0	POWER_FAIL	
F	ATA_D_MACK	ATA_C_S1	SFS4			NVCC5	BATT_L_INE	USBOT_G_DAT_A6	USBOT_G_DAT_A0	RXD1	RI_DC_E1	DTR_D_CE2	KEY_R_OW0	KEY_R_OW6	KEY_C_OL6	TDI	STX0	GPIO1_0	GPIO1_4	BOOT_MODE0	GND			CKIH	GPIO1_3	VSTBY	
G	PWMO	PC_RW	CSP13_MISO			CSP13_SPLR_DY	NVCC5		USBOT_G_CLK	USBOT_G_DAT_A2	RTS1	RI_DT_E1	CTS2	KEY_R_OW4	KEY_C_OL2	TMS	SIMPD0	COMPARE	NVCC1				DVFS1	VPG0	CLKSS		
H	PC_RS	PC_BV_T	ATA_R_D1	ESET		ATA_DI_OW																CKIL			POR	I2C_DA_T	GPIO3_1
J	PC_VS_1	PC_RE_ADY	IOIS16			ATA_C_S0	PC_PO_E		QVCC1	QVCC1	NVCC8	NVCC8	QVCC	NVCC6	NVCC6	NVCC6	NVCC9		VPG1	RESET_IN			I2C_CL_K	CSI_VS_YNC	CSI_PIX_CLK		
K	PC_CD_2	SD1_D_ATA3	PC_PW_RON			PC_BV_D2	PC_VS_2	QVCC1						NVCC6		NVCC1		CSI_H_SYNC_0	GPIO3_0			CSI_MC_LK	CSI_D5	CSI_D7			
L	SD1_D_ATA1	SD1_C_SD1_D_MD	SD1_D_ATA2			PC_WA_IT	PC_CD_1	NVCC3		QVCC1	GND	QVCC	QVCC	QVCC	QVCC	QVCC	NVCC4	NVCC4	CSI_D8	CSI_D4			CSI_D6	CSI_D9	CSI_D1_1		
M	USBH2_DATA0	USBH2_STP	USBH2_DATA1			SD1_D_ATA0	SD1_C_LK	NVCC3		GND	GND	GND	GND	GND	GND	GND	QVCC		CSI_D1_4	CSI_D1_2			CSI_D1_0	CSI_D1_3	CSI_D1_5		
N	USBH2_CLK	CSP11_SCLK	CSP11_SPI_RDY			USBH2_NXT_DIR	USBH2	QVCC4	NVCC3	GND	GND	GND	GND	GND	GND	GND	NVCC7		SD_D_FPSHIFT			VSYNC_0	HSYNC	DRDY0			
P	CSP11_SS1	CSP11_MOSI	CSP11_SS0			CSP11_SS2	CSP11_MISO	NVCC1_0	NVCC1_0	GND	GND	GND	GND	GND	GND	GND	NVCC7		READ	LCS1			SD_D_CLK_O	SD_D_I	LCS0		
R	STXD3	SCK3	SRXD3			SFS3	SRXD6	QVCC4	NVCC1_0	GND	GND	GND	GND	GND	GND	GND	NVCC7		D3_CL_S	PAR_RS			CONTRAST	WRITE_3	VSYNC_3		
T	STXD6	SCK6	SFS6			NFCE	NFWF	QVCC4	NVCC1_0	GND	GND	SGND	MGND	UGND		NVCC7		LD4	LD2			LD0	SER_RS	D3_REV			
U	NFRB	NFWF	NFCLE			D15	D11	QVCC4									QVCC		TTM_PAD	LD8			LD6	D3_SPL	LD1		
V	NFALE	NFRE	D13			D9	D5	QVCC	QVCC	QVCC	QVCC	SVCC	MVCC	UVCC	GND			LD17	LD13			LD10	LD3	LD5			
W	D14	D12	D7			D3	NVCC2_2														EB0			LD15	LD7	LD9	
Y	D10	D8	D1			IOQVD_D	NVCC2_2	NVCC2_2	NVCC2_2	NVCC2_2	NVCC2_2	NVCC2_1	NVCC2_1	NVCC2_1	NVCC2_1	NVCC2_1	NVCC2_1	NVCC2_1	NVCC2_1	NVCC2_1	M_GRANT			EB1	LD11	LD12	
AA	D6	D4	A4			NVCC2_2	SD31	SD28	SD27	SD23	SD21	SD18	SD16	SD13	SD9	SD7	SD5	SD3	SD2	DQM2	SDCLK			FVCC	LD14	LD16	
AB	D2	D0	A6			A2															RW			FGND	OE	BCLK	
AC	MA10	GND	A11																					FUSE_VDD	M_REQUEST	GND	
AD	GND	GND	A12	A13	A8	A0	SDBA0	SDQS3	SD29	SD25	SDQS2	SD17	SD15	SD12	SD8	SDQSO	SD4	SD0	DQM1	CAS_0	SDCKE	CS3	ECB	GND	GND	GND	
AE	GND	GND	A7	A3	SDBA1	SD30	SD26	SD24	SD22	SD20	SD19	SDQS1	SD14	SD11	SD10	SD6	SD1	DQM3	DQM0	SDCLK	CS2	LBA	CS0	GND	GND	GND	
AF	GND	GND	A9	A5	A1	A25	A24	A23	A22	A21	A20	A19	A18	A17	A16	A15	A14	A10	RAS	SDWE	SDCKE_1	CS5	CS1	CS4	GND	GND	